

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Kirk D. Prall, et al.

Serial No: 09/503,638

Filed: February 14, 2000

For: RANDOM ACCESS MEMORY

Attorney

Docket Number: MICR131.02

Group Art Unit: 2814

Examiner: G. Peralta

*10/c
T. Steptoe
9-20-02*

September 17, 2002

FAX COPY RECEIVED

Assistant Commissioner of Patents
Washington, DC 20231

SEP 17 2002

TECHNOLOGY CENTER 2800

Sir:

RESPONSE TO THE OFFICE ACTION MAILED JUNE 19, 2002

Please amend the Application as follows.

In The Claims

Cancel Claim 29.

Substitute the following amended claims for the original claims having the same number.

26.(amended once) A semiconductor memory device, comprising:
a silicon structure having a first conductivity type;
a gate electrode over the silicon structure;
a capacitor contact region in the silicon structure adjacent to one side of the gate electrode;
a bit line contact region in the silicon structure adjacent to the other side of the gate electrode;
a first dopant implant in the capacitor and bit line contact regions, the first dopant having a second conductivity type opposite the first conductivity type;
insulating spacers extending along the sidewalls of the gate electrode and over a portion of the first dopant implant in the capacitor and bit line contact regions; and

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